

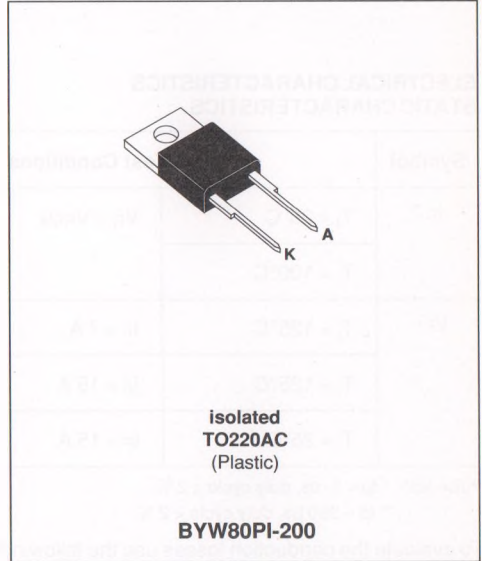
HIGH EFFICIENCY FAST RECOVERY RECTIFIER DIODES

FEATURES

- SUITED FOR SMPS
- VERY LOW FORWARD LOSSES
- NEGLIGIBLE SWITCHING LOSSES
- HIGH SURGE CURRENT CAPABILITY
- HIGH AVALANCHE ENERGY CAPABILITY
- INSULATED PACKAGE :
Insulating voltage = 2500 V_{RMS}
Capacitance = 7 pF

DESCRIPTION

Single chip rectifier suited for switchmode power supply and high frequency DC to DC converters. Packaged in Isolated TO220AC, this device is intended for use in low voltage, high frequency inverters, free wheeling and polarity protection applications.



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter		Value	Unit
I _{F(RMS)}	RMS forward current		20	A
I _{F(AV)}	Average forward current $\delta = 0.5$	T _c = 110°C	10	A
I _{FSM}	Surge non repetitive forward current	t _p = 10ms sinusoidal	100	A
T _{stg} T _j	Storage and junction temperature range		- 65 to + 150 - 65 to + 150	°C °C

Symbol	Parameter	BYW80PI-				Unit
		50	100	150	200	
V _{RRM}	Repetitive peak reverse voltage	50	100	150	200	V

THERMAL RESISTANCE

Symbol	Parameter	Value	Unit
Rth (j-c)	Junction to case	3.5	°C/W

ELECTRICAL CHARACTERISTICS
STATIC CHARACTERISTICS

Symbol	Test Conditions		Min.	Typ.	Max.	Unit
I _R *	T _j = 25°C	V _R = V _{RRM}			10	μA
	T _j = 100°C				1	mA
V _F **	T _j = 125°C	I _F = 7 A			0.85	V
	T _j = 125°C	I _F = 15 A			1.05	
	T _j = 25°C	I _F = 15 A			1.15	

Pulse test : * tp = 5 ms, duty cycle < 2 %

** tp = 380 μs, duty cycle < 2 %

To evaluate the conduction losses use the following equation :

$$P = 0.65 \times I_{F(AV)} + 0.027 \times I_{F(RMS)}^2$$

RECOVERY CHARACTERISTICS

Symbol	Test Conditions		Min.	Typ.	Max.	Unit
trr	T _j = 25°C	I _F = 0.5A I _R = 1A			25	ns
		I _F = 1A V _R = 30V			35	
tfr	T _j = 25°C	I _F = 1A V _{FR} = 1.1 x V _F		15		ns
V _{FP}	T _j = 25°C	I _F = 1A tr = 10 ns		2		V

Fig.1 : Average forward power dissipation versus average forward current.

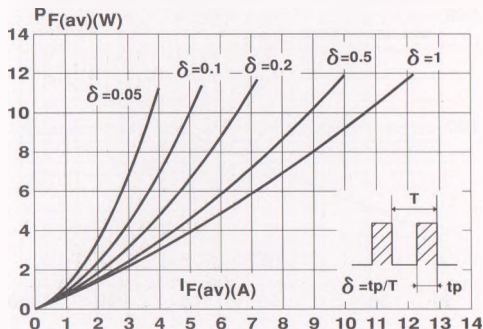


Fig.2 : Peak current versus form factor.

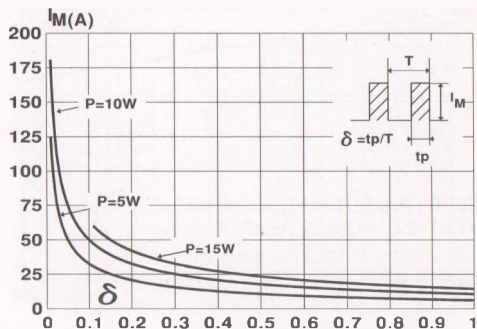


Fig.3 : Forward voltage drop versus forward current (maximum values).

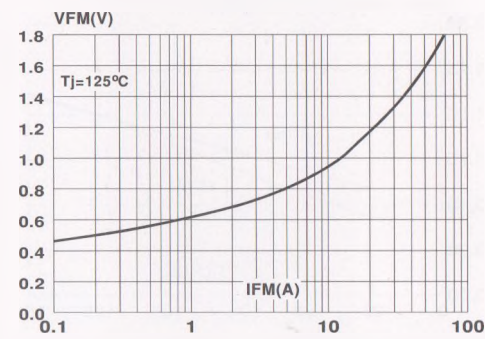


Fig.4 : Relative variation of thermal impedance junction to case versus pulse duration.

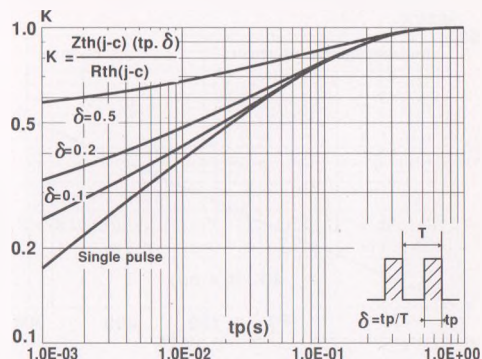


Fig.5 : Non repetitive surge peak forward current versus overload duration.

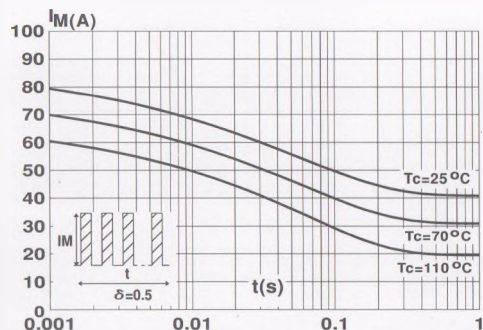


Fig.6 : Average current versus ambient temperature. (duty cycle : 0.5)

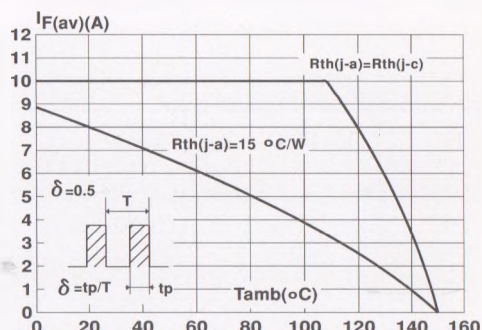


Fig.7 : Junction capacitance versus reverse voltage applied (Typical values).

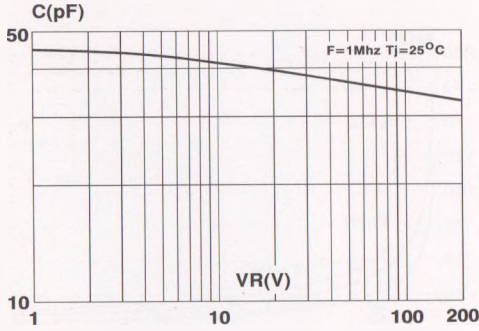


Fig.8 : Recovery charges versus dI_F/dt .

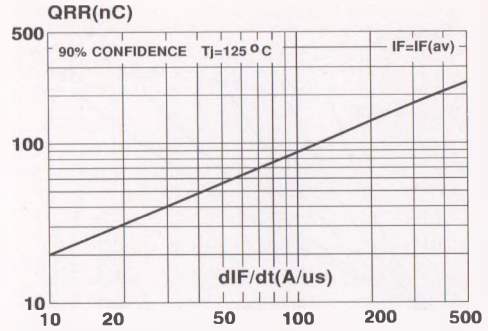


Fig.9 : Peak reverse current versus dI_F/dt .

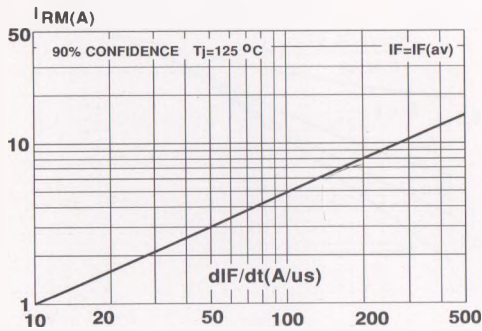


Fig.10 : Dynamic parameters versus junction temperature.

